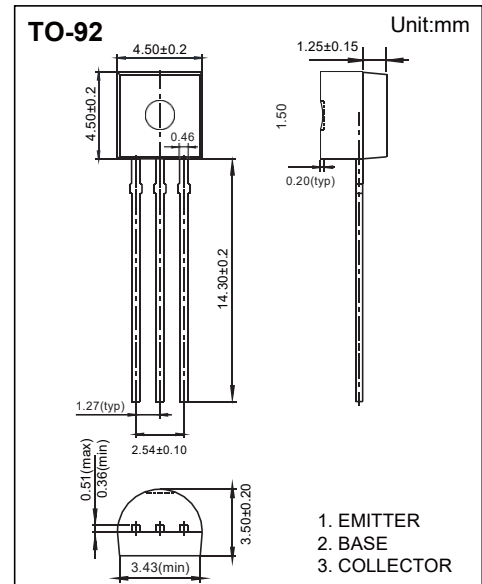


Transistor

PNP Transistors 2N5401

■ Features

- Switching and Amplification in High Voltage
- Applications such as Telephony
- Low Current
- High Voltage



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-160	V
Collector - Emitter Voltage	V _{CE0}	-150	
Emitter - Base Voltage	V _{EB0}	-5	
Collector Current - Continuous	I _C	-0.6	A
Collector Power Dissipation	P _C	625	mW
Thermal Resistance From Junction To Ambient	R _{θJA}	200	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to 150	

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■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collecto- base breakdown voltage	V _{CB0}	I _C = -100 μA, I _E =0	-160			V
Collector- emitter breakdown voltage	V _{CE0}	I _C = -1 mA, I _B =0	-150			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _C =0	-5			
Collector cut-off current	I _{CBO}	V _{CB} = -120 V, I _E =0			-0.05	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -3V, I _C =0			-0.05	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-50 mA, I _B = -5mA			-0.5	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-50 mA, I _B = -5mA			-1	
DC current gain	h _{FE(1)}	V _{CE} = -5V, I _C = -1mA	80			
	h _{FE(2)}	V _{CE} = -5V, I _C = -10mA	60		300	
	h _{FE(3)}	V _{CE} = -5V, I _C = -50mA	50			
Transition frequency	f _T	V _{CE} = -5V, I _C = -10mA, f=30MHz	100		300	MHz

Note:Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.

■ Classification of hFE(2)

Rank		A	B	C
Range	60-100	100-150	150-200	200-300

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■ Typical Characteristics

